

Halogens free devices



CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

N-Channel Enhancement Mode Field Effect Transistor

VOLTAGE 60 Volts CURRENT 4.0 Ampere

CHM3055ZGP

APPLICATION

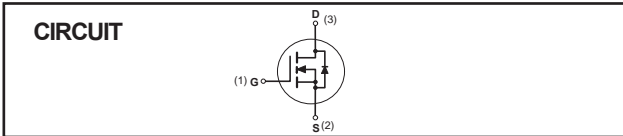
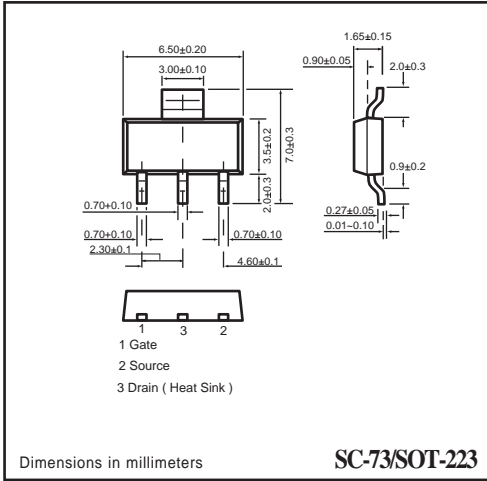
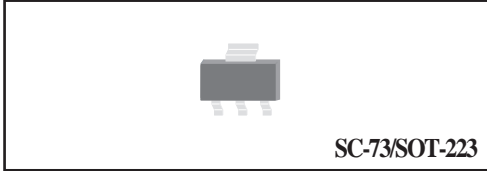
- * Servo motor control.
- * Power MOSFET gate drivers.
- * Other switching applications.

FEATURE

- * Small package. (SC-73/SOT-223)
- * High density cell design for extremely low $R_{DS(ON)}$.
- * Rugged and reliable.

CONSTRUCTION

- * N-Channel Enhancement



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	CHM3055ZGP	Units
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Maximum Drain Current - Continuous	4.0	A
	- Pulsed (Note 3)	25	
P_D	Maximum Power Dissipation	3000	mW
T_J	Operating Temperature Range	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Note : 1. Surface Mounted on FR4 Board , $t \leq 10\text{sec}$
 2. Pulse Test , Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
 3. Repetitive Rating , Pulse width limited by maximum junction temperature
 4. Guaranteed by design , not subject to production trsting

Thermal characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	42	$^\circ\text{C/W}$
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ELECTRICAL CHARACTERISTIC (CHM3055ZGP)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}$			10	μA
I_{GSSF}	Gate-Body Leakage	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			+100	nA
I_{GSSR}	Gate-Body Leakage	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

ON CHARACTERISTICS (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2		4	V
$R_{DS(on)}$		$V_{GS} = 10\text{ V}, I_D = 4.0\text{ A}$		75	100	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 4.0\text{ A}$	3	4		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		335		pF
C_{oss}	Output Capacitance			150		
C_{riss}	Reverse Transfer Capacitance			40		

SWITCHING CHARACTERISTICS (Note 4)

Q_g	Total Gate Charge	$V_{DS} = 48\text{ V}, I_D = 4.0\text{ A}$ $V_{GS} = 10\text{ V}$		10	13	nC
Q_{gs}	Gate-Source Charge			2.4		
Q_{gd}	Gate-Drain Charge			4.0		
t_{on}	Turn-On Time	$V_{DD} = 25\text{ V}$ $I_D = 1.2\text{ A}, V_{GS} = 10\text{ V}$ $R_{GEN} = 50\ \Omega$		17	25	nS
t_r	Rise Time			24	50	
t_{off}	Turn-Off Time			41	65	
t_f	Fall Time			33	60	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I_S	Drain-Source Diode Forward Current	(Note 1)			2.5	A
V_{SD}	Drain-Source Diode Forward Voltage	$I_S = 4.0\text{ A}, V_{GS} = 0\text{ V}$ (Note 2)			1.2	V